

Silicon PNP Power Transistors

2SB861

DESCRIPTION

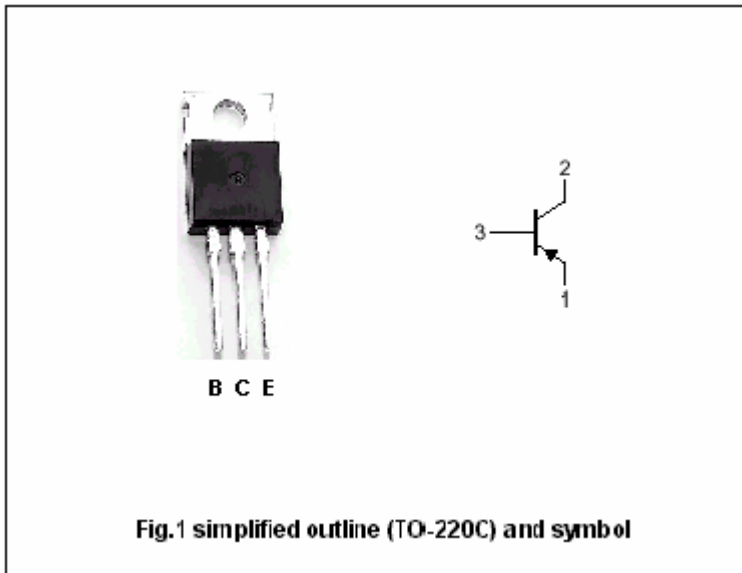
- With TO-220C package
- Complement to type 2SD1138

APPLICATIONS

- Low frequency power amplifier color TV vertical deflection output

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-200	V
V _{CEO}	Collector-emitter voltage	Open base	-150	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current		-2	A
I _{CP}	Collector current-Peak		-5	A
P _C	Collector power dissipation	T _a =25°C	1.8	W
		T _C =25°C	30	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-45~150	°C

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA; R_{BE}=\infty$	-150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-5mA; I_C=0$	-6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-0.5A; I_B=-50mA$			-3.0	V
V_{BE}	Base-emitter voltage	$I_C=-50mA; V_{CE}=-4V$			-1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-120V; I_E=0$			-1	μA
h_{FE-1}	DC current gain	$I_C=-50mA; V_{CE}=-4V$	60		200	
h_{FE-2}	DC current gain	$I_C=-0.5A; V_{CE}=-10V$	60			
C_{OB}	Output capacitance	$I_E=0; V_{CB}=-100V, f=1MHz$		30		pF

◆ h_{FE-1} classifications

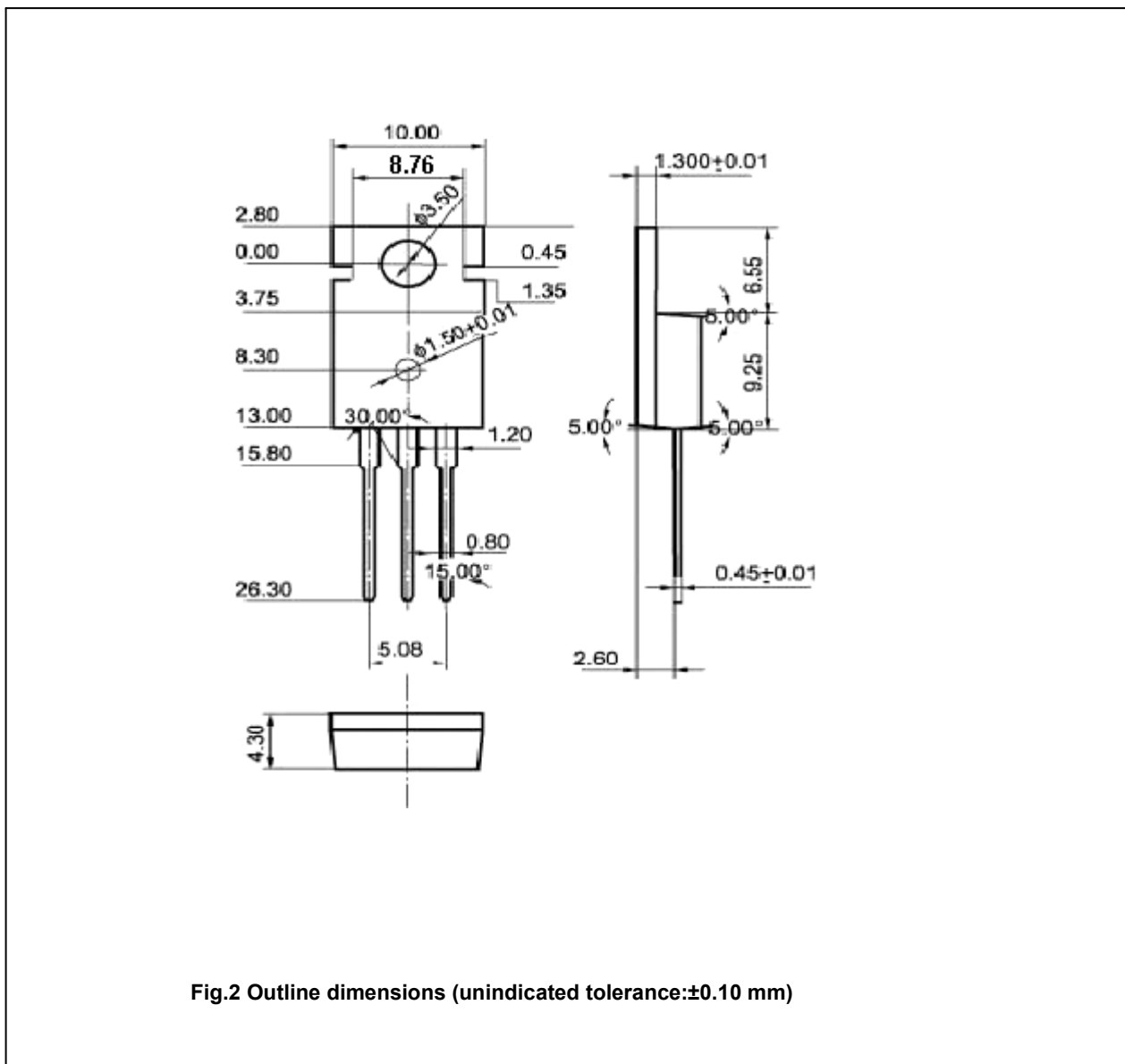
B	C
60-120	100-200

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PACKAGE OUTLINE



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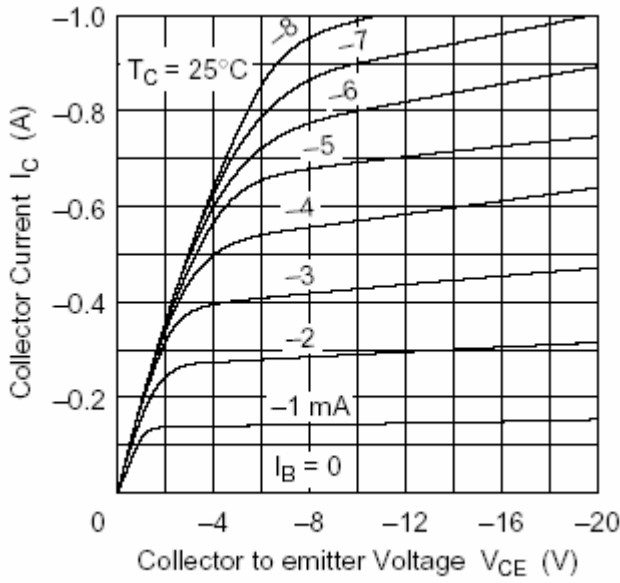


Fig.3 Static Characteristic

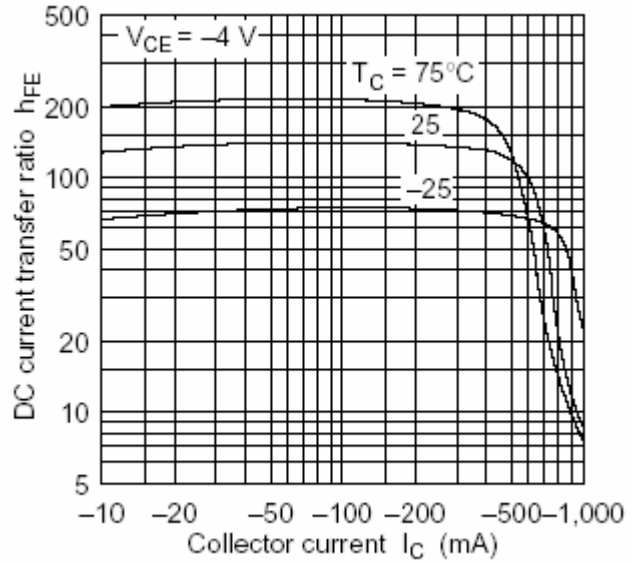


Fig.4 DC current Gain

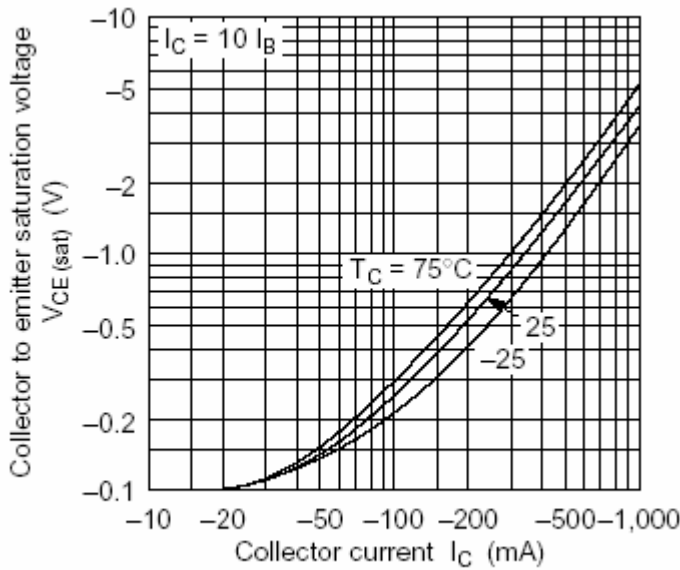


Fig.5 Collector-Emitter Saturation Voltage

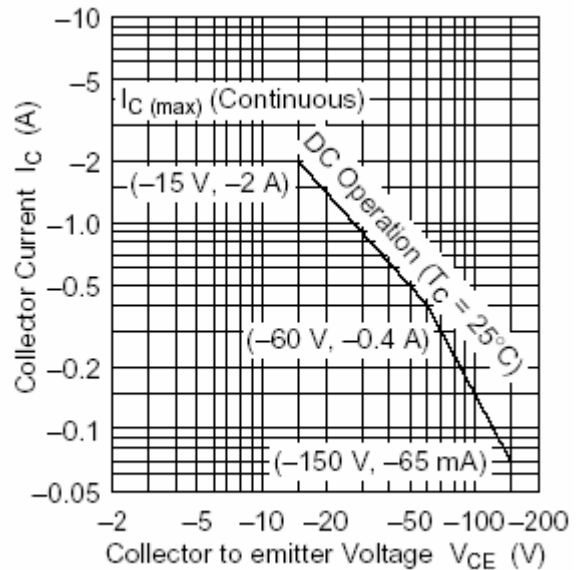


Fig.6 Safe Operating Area